

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application. No new matter has been added.

Listing of Claims:

1. (Currently Amended) A process for treating an exhaust gas let out from CVD system for forming a silicon film using halogenosilane gas, the process comprising the steps of:

subjecting an unreacted raw gas and intermediate products included in the exhaust gas to a partial decomposition or conversion reaction treatment using a heated transition metal reacting agent ~~for thermal swing between room temperature and 500°C;~~

separating and recovering the obtained halogenosilane gas and hydrogen chloride gas; and

returning at least one of the halogenosilane gas and hydrogen chloride gas to a raw gas source for the CVD system.

2. (Currently Amended) A process for treating an exhaust gas let out from CVD system for forming a silicon film using halogenosilane gas, the process comprising the steps of:

subjecting an unreacted raw gas and intermediate products included in the exhaust gas to a full decomposition or conversion reaction treatment using a ~~transition metal~~ an iron reacting agent for thermal-swing between room temperature and 500°C; and

separating and recovering contacting the obtained hydrogen chloride gas of the decomposed product with water; and

recovering the hydrochloric acid water.

3. (Withdrawn) An apparatus for treating an exhaust gas let out from CVD system for forming a silicon film using halogenosilane gas, the apparatus comprising:

decomposition means for subjecting a transition metal reacting agent to thermal-swing between room temperature and 500°C to partially decompose an unreacted raw gas and intermediate products contained in the exhaust gas;

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separation reaction means for separating the halogenosilane gas and hydrogen chloride from the exhaust gas let out from said decomposition means;

vapor-liquid contacting means for bring the hydrogen chloride separated by said separation reaction means into contact with water; and

gas recovery means for reusing the halogenosilane.

4. (Withdrawn) An apparatus for treating an exhaust gas let out from CVD system for forming a silicon film using halogenosilane gas, the apparatus comprising:

decomposition means for subjecting a transition metal reacting agent for thermal-swing between room temperature and 500°C to entirely decompose an unreacted raw gas and intermediate products contained in the exhaust gas; and

vapor-liquid contacting means for bring the hydrogen chloride separated by said separation reaction means into contact with water.